

SST4416 N-CHANNEL JFET



Linear Systems replaces discontinued Siliconix SST4416 The SST4416 is a N-Channel high frequency JFET amplifier

The SST4416 N-channel JFET is designed to provide high-performance amplification at high frequencies.

The SOT-23 package provides ease of manufacturing, and a lower cost assembly option.

SST4416 Benefits:

- Wideband High Gain
- Very High System Sensitivity
- High Quality of Amplification
- High-Speed Switching Capability
- High Low-Level Signal Amplification

SST4416 Applications:

- High-Frequency Amplifier / Mixer
- Oscillator
- Sample-and-Hold
- Very Low Capacitance Switches

FEATURES					
DIRECT REPLACEMENT FOR SILICONIX SST4416					
EXCEPTIONAL GAIN (400 MHz)	10dB (min)				
VERY LOW NOISE FIGURE (400 MHz)	4dB (max)				
VERY LOW DISTORTION					
HIGH AC/DC SWITCH OFF-ISOLATION					
ABSOLUTE MAXIMUM RATINGS					
@ 25°C (unless otherwise noted)					
Maximum Temperatures					
Storage Temperature	-65°C to +200°C				
Operating Junction Temperature	-55°C to +135°C				
Maximum Power Dissipation					
Continuous Power Dissipation	300mW				
MAXIMUM CURRENT					
Gate Current (Note 1)	10mA				
MAXIMUM VOLTAGES					
Gate to Drain or Gate to Source	-30V				

SST4416 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS	
BV_{GSS}	Gate to Source Breakdown Voltage	-30		-	V	$I_{G} = -1\mu A$, $V_{DS} = 0V$	
$V_{GS(off)}$	Gate to Source Cutoff Voltage			-6	V	$V_{DS} = 15V, I_{D} = 1nA$	
I _{DSS}	Gate to Source Saturation Current	5	4-	1 5	mA	$V_{DS} = 15V, V_{GS} = 0V$	
I _{GSS}	Gate <mark>Le</mark> akage Current			-1.0	nA	$V_{GS} = -15V, V_{DS} = 0V$	
g _{fs}	Forward <mark>T</mark> rans <mark>co</mark> nd <mark>uc</mark> tance	4500		750 <mark>0</mark>	μS	$V_{DS} = 15V, V_{GS} = 0V, f = 1kHz$	
g _{os}	Outp <mark>ut</mark> Con <mark>d</mark> uct <mark>an</mark> ce			50	μS		
C _{iss}	Input Capacitance ²			0.8	pF		
C_{rss}	Reverse Transfer Capacitance ²			4	pF	$V_{DS} = 15V, \ V_{GS} = 0V, f = 1MHz$	
C _{oss}	Output Capacitance ²			2	pF		
e _n	Equivalent Input Noise Voltage		6		nV/√Hz	$V_{DS} = 10V$, $V_{GS} = 0V$, $f = 1kHz$	

SST4416 HIGH FREQUENCY ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	100 Mhz		400 [Mhz	UNITS	CONDITIONS	
		MIN	MAX	MIN	MAX			
g _{Iss}	Input Conductance		100		1000			
b _{iss}	Input Susceptance ²		2500		10000	c	$V_{DS} = 15V, V_{GS} = 0V$	
g _{oss}	Output Conductance		75		100	μS	V _{DS} - 13V, V _{GS} - UV	
b _{oss}	Output Susceptance ²		1000		4000			
G _{fs}	Forward Transconductance			4000				
G _{ps}	Power Gain ²	18		10		dB	$V_{DS} = 15V$, $I_D = 5mA$	
NF	Noise Figure ²		2		4		$V_{DS} = 15V$, $I_D = 5mA$, $R_G = 1k\Omega$	
NOTES	1. Absolute maximum ratings are limiting values above which SSTAALS convice ability may be impaired							

1. Absolute maximum ratings are limiting values above which SST4416 serviceability may be impaired.

2. Not production tested, guaranteed by design

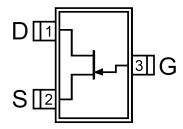
Micross Components Europe



Available Packages:

SST4416 in SOT-23 SST4416 in bare die.

SOT-23 (Top View)



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Please contact Micross for full package and die dimensions

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